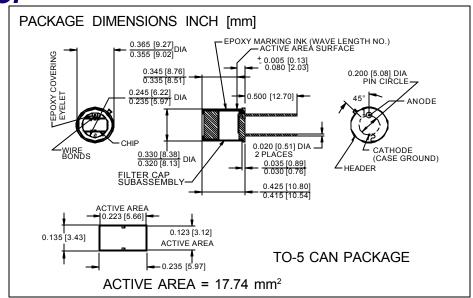
PHOTONIC
Silicon Photodiode, Filter Combination Photovoltaic
DETECTORS INC. (center wavelength 436 nm) Type PDB-V443.6





RESPONSIVITY (A/W)

FEATURES

- 436 +/- 2 nm CWL
- 10 nm FWHM
- 45% transmission
- 10⁻⁴ rejection

DESCRIPTION

The **PDB-V443.6** is a silicon, PIN planar diffused, photodiode with a narrow band interference filter. The detector filter combination has a narrow 10 nm half bandwidth designed for low noise photovoltaic applications. Packaged in a TO-5 metal can.

APPLICATIONS

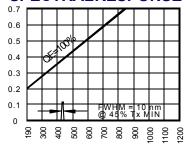
- Spectrophotometry
- Chemistry instrumentation
- Liquid chromatography

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		100	V
T_{STG}	Storage Temperature	-20	+85	∘C
То	Operating Temperature Range	-15	+70	⊙C
Ts	Soldering Temperature*		+240	∘C
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE



WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
Isc	Short Circuit Current***	H = 100 fc, 2850 K	150	200		μ A			
ΙD	Dark Current	$H = 0, V_R = 10 \text{ mV}$		10	50	pA			
RsH	Shunt Resistance	H = 0, V _R = 10 mV	.20	2		GΩ			
TC Rsh	Rsh Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃			
Сл	Junction Capacitance	H = 0, V _R = 10 V**		1700		pF			
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		436		nm			
HBW	Half Bandwidth	(FWHM)		10		nm			
V _{BR}	Breakdown Voltage	I = 10 μA	50	75		V			
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		9x10 ⁻¹⁵		W/ √ Hz			
tr	Response Time	RL = 1 KΩ V _R = 10 V		1.0		μS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f=1 MHz, ***without filter [FORM NO. 100-PDB-V443.6 REV N/C]